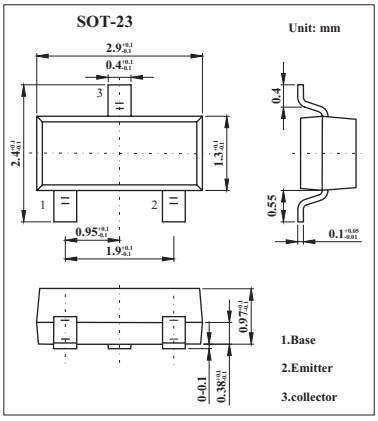
Silicon NPN Triple Diffused Type

2SC4497



■ Features

- High voltage.
- Low saturation voltage.
- Small collector output capacitance.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	300	V
Collector-emitter voltage	V_{CEO}	300	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	100	mA
Base current	I_B	20	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 300 V, I_E = 0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 6 V, I_C = 0			0.1	μA
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 0.1 mA, I_E = 0	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1 mA, I_B = 0	300			V
DC current gain	h_{FE}	V_{CE} = 10 V, I_C = 20 mA	30		150	
		V_{CE} = 10 V, I_C = 1mA	20			
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 20 mA, I_B = 2 mA			0.5	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C = 20 mA, I_B = 2 mA			1.2	V
Transition frequency	f_T	V_{CE} = 10 V, I_C = 10 mA		70		MHz
Collector output capacitance	C_{ob}	V_{CB} = 20 V, I_E = 0, f = 1 MHz		3	4	pF

■ h_{FE} Classification

Marking	3R	3O
Rank	R	O
hFE	30～90	50～150